

Title (en)

REACTOR FOR CARRYING OUT AN ETCHING METHOD FOR A STACK OF MASKED WAFERS AND AN ETCHING METHOD

Title (de)

REAKTOR ZUR DURCHFÜHRUNG EINES ÄTZVERFAHRENS FÜR EINEN STAPEL VON MASKIERTEN WAFERN UND ÄTZVERFAHREN

Title (fr)

REACTEUR POUR LA MISE EN OEUVRE D'UN PROCEDE DE GRAVURE POUR UNE PILE DE TRANCHES MASQUEES ET PROCEDE DE GRAVURE ASSOCIE

Publication

EP 1902456 A1 20080326 (DE)

Application

EP 06763323 A 20060529

Priority

- EP 2006062664 W 20060529
- DE 102005031602 A 20050706

Abstract (en)

[origin: WO2007003473A1] The reactor (11) for carrying out a method for etching a stack of masked wafers (1) with the aid of an etching gas, preferably a chlorotrifluoride (ClF₃), is characterised in that it comprises a device for carrying out a plasma processing device (15). The inventive method for etching masked wafers with the aid of the etching gas, preferably a chlorotrifluoride (ClF₃), consists in pre-processing the wafers by a plasma process, prior to the etching process, wherein said methods are characterised in that the pre-processing of wafers and the process for etching the stack of wafers are carried out in a reactor chamber.

IPC 8 full level

H01J 37/34 (2006.01); **H01J 37/32** (2006.01); **H01L 21/00** (2006.01); **H01L 21/311** (2006.01)

CPC (source: EP US)

H01J 37/32532 (2013.01 - EP US); **H01J 37/34** (2013.01 - EP US); **H01L 21/67069** (2013.01 - EP US); **H01J 2237/3341** (2013.01 - EP US)

Citation (search report)

See references of WO 2007003473A1

Citation (examination)

- JP H11243080 A 19990907 - NEC CORP
- US 2005045276 A1 20050303 - PATEL SATYADEV R [US], et al

Designated contracting state (EPC)

DE FR IT

DOCDB simple family (publication)

DE 102005031602 A1 20070111; EP 1902456 A1 20080326; JP 2009500836 A 20090108; US 2010006427 A1 20100114;
WO 2007003473 A1 20070111

DOCDB simple family (application)

DE 102005031602 A 20050706; EP 06763323 A 20060529; EP 2006062664 W 20060529; JP 2008519887 A 20060529;
US 98849706 A 20060529